

**REMARKS**

Claims 1-23 are pending in this application. No amendment is made in this Response. It is believed that this Amendment is fully responsive to the Office Action dated **June 5, 2008**.

**Claims 1, 4, 5, and 9-12 are rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094. (Office action paragraph no. 2)**

**Claim 2 is rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094, and further in view of Adkisson et al. '202. (Office action paragraph no. 3)**

**Claim 6 is rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094, and further in view of Kim et al. '371. (Office action paragraph no. 4)**

**Claim 7 is rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094, and further in view of Greenwald et al. '026. (Office action paragraph no. 5)**

**Claim 8 is rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094, and further in view of Yamawaki et al. '774. (Office action paragraph no. 6)**

**Claims 13-18 and 20-22 are rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094, and further in view of Li '254. (Office action paragraph no. 7)**



**Claims 19 and 23 are rejected under 35 U.S.C. §103(a) as being unpatentable over Takeshi et al. (Abstract JP 8186235) in view of Mirkarimi et al. '094, further in view of Li '254, and further in view of Lee et al. '705. (Office action paragraph no. 8)**

These rejections are respectfully traversed, and reconsideration of the rejections is requested.

Claim 1 is the base claim for all of the pending claims in this application. In claim 1, a "ferroelectric single crystalline thin film" is epitaxially formed on a single crystalline substrate. The "ferroelectric single crystalline thin film" formed is a single crystal having no grain boundary.

In contrast, Takeshi et al., cited by the Examiner, does not disclose use of a film of "single" crystal, although the Examiner alleged that Takeshi et al. discloses the formation of a ferroelectric single thin film.

Thus, claim 1 and dependent claims 2-23 are not obvious over Takeshi et al., Mirkarimi et al., and the other cited references, taken separately or in combination.

If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact the applicants' undersigned agent at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.



U.S. Patent Application Serial No. **10/532,249**

Response filed September 22, 2008

Reply to OA dated June 5, 2008

In the event that this paper is not timely filed, the applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

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Enclosure: Petition for Extension of Time

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